

LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S
INFORMATION DISCLOSURE STATEMENTApplicant:
D. Chidambarrao, et al.

(Use several sheets if necessary)

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Filing Date:
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2822

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINERS INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
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OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

REP		Kern Rim, et al., "Transconductance Enhancement in Deep Submicron Strained-Si <i>n</i> -MOSFETs", International Electron Devices Meeting, 26, 8, 1, IEEE, September 1998.
REP		Kern Rim, et al., "Characteristics and Device Design of Sub-100 nm Strained Si N- and PMOSFETs", 2002 Symposium On VLSI Technology Digest of Technical Papers, IEEE, pp 98-99.
REP		Gregory Scott, et al., "NMOS Drive Current Reduction Caused by Transistor Layout and Trench Isolation Induced Stress", International Electron Devices Meeting, 34.4.1, IEEE, September 1999.
REP		F. Ootsuka, et al., "A Highly Dense, High-Performance 130nm node CMOS Technology for Large Scale System-on-a-Chip Application", International Electron Devices Meeting, 23.5.1, IEEE, April 2000.
REP		Shinya Ito, et al., "Mechanical Stress Effect of Etch-Stop Nitride and its Impact on Deep Submicron Transistor Design", International Electron Devices Meeting, 10.7.1, IEEE, April 2000.
REP		A. Shimizu, et al., "Local Mechanical-Stress Control (LMC): A New Technique for CMOS-Performance Enhancement", International Electron Devices Meeting, IEEE, March 2001.
REP		K. Ota, et al., "Novel Locally Strained Channel Technique for high Performance 55nm CMOS", International Electron Devices Meeting, 2.2.1, IEEE, February 2002.

EXAMINER



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